



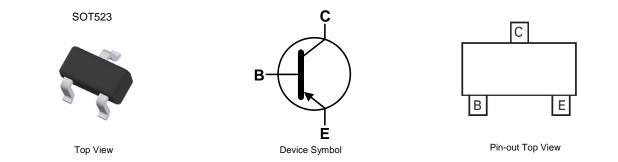
### 40V PNP SMALL SIGNAL TRANSISTOR IN SOT523

## Features

- BV<sub>CEO</sub> > -40V
- I<sub>C</sub> = -200mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMBT3904T
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.002 grams (Approximate)



## Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMBT3906T-7-F	NRND	AEC-Q101	3N	7	8	3,000
MMBT3906T-13-F	NRND	AEC-Q101	3N	13	8	10,000
MMBT3906T-7	Active	AEC-Q101	3N	7	8	3,000
MMBT3906T-13	Active	AEC-Q101	3N	13	8	10,000

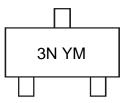
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. NRND = Not Recommended for New Design. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



 $\begin{array}{l} 3N = \mbox{Product Type Marking Code} \\ YM = \mbox{Date Code Marking} \\ Y \mbox{ or } \overline{Y} = \mbox{Year (ex: C = 2015)} \\ M \mbox{ or } \overline{M} = \mbox{Month (ex: 9 = September)} \end{array}$ 

Date Code Key

Year	2015	5	2016	2017	2018	2019	2020	202	1 20	22	2023	2024	2025
Code	С		D	E	F	G	Н			J	К	L	М
Mont	h	Jai	n Fel	o Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	•	1	2	3	4	5	6	7	8	9	0	N	D



# Absolute Maximum Ratings ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	lc	-200	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ extsf{ heta}JA}$	833	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

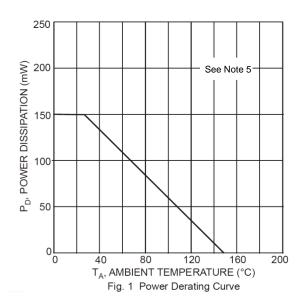
## ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## Thermal Characteristics and Derating Information





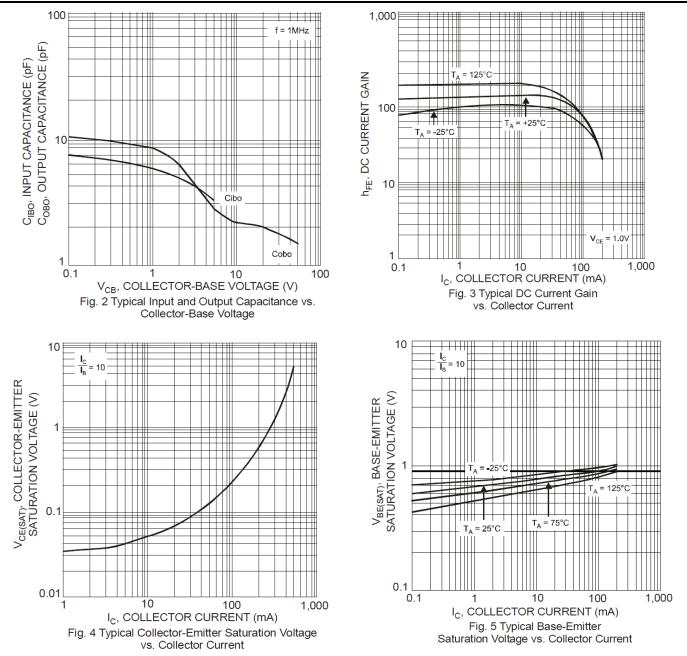
# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					·
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40		V	$I_{C} = -10\mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-40	_	V	$I_{\rm C} = -1 {\rm mA},  I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	_	V	$I_{E} = -10\mu A$ , $I_{C} = 0$
Collector Cutoff Current	I <sub>CEX</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3V$
Base Cutoff Current	I <sub>BL</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3V$
ON CHARACTERISTICS (Note 7)					•
DC Current Gain	h <sub>FE</sub>	60 80 100 60 30	 300 	_	$\begin{split} I_{C} &= -100 \mu A, \ V_{CE} &= -1V \\ I_{C} &= -1mA, \ V_{CE} &= -1V \\ I_{C} &= -10mA, \ V_{CE} &= -1V \\ I_{C} &= -50mA, \ V_{CE} &= -1V \\ I_{C} &= -100mA, \ V_{CE} &= -1V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.25 -0.40	V	$I_{C} = -10mA$ , $I_{B} = -1mA$ $I_{C} = -50mA$ , $I_{B} = -5mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65	-0.85 -0.95	V	$I_{C} = -10mA$ , $I_{B} = -1mA$ $I_{C} = -50mA$ , $I_{B} = -5mA$
SMALL SIGNAL CHARACTERISTICS			1		1
Output Capacitance	C <sub>obo</sub>	_	4.5	pF	$V_{CB} = -5V, f = 1.0MHz, I_E = 0$
Input Capacitance	C <sub>ibo</sub>	_	10	pF	$V_{EB} = -0.5V, f = 1.0MHz, I_{C} = 0$
nput Impedance	h <sub>ie</sub>	2	12	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>	$V_{CE} = -10V, I_{C} = -10mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400	—	f = 1.0MHz
Output Admittance	h <sub>oe</sub>	3	60	μS	
Current Gain-Bandwidth Product	f⊤	250	—	MHz	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$
Noise Figure	NF		5	dB	$V_{CC} = 5V$ , $I_C = 100\mu A$ , $R_S = 1k\Omega$ , $f = 1MHz$
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>D</sub>	_	35	ns	$V_{CC} = -3V, I_{C} = -10mA,$
Rise Time	t <sub>R</sub>	_	35	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = -1mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA$
Fall Time	t <sub>F</sub>	_	75	ns	$I_{B1} = -I_{B2} = -1.0$ mA

Note: 7. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



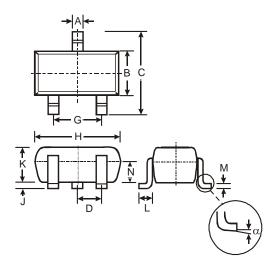
## **Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

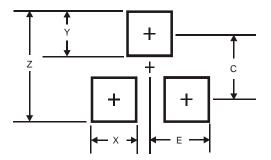
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT523						
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
C	1.45	1.75	1.60				
D	_	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
κ	0.60	0.80	0.75				
L	0.10	0.30	0.22				
Μ	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	0°	8°					
All	Dimens	ions in	mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7



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